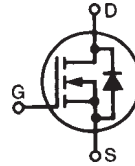


TrenchT2™ Power MOSFET

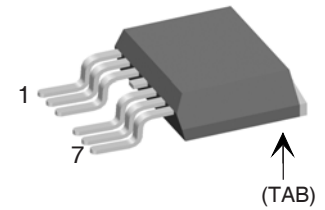
IXTA220N04T2-7

$V_{DSS} = 40V$
 $I_{D25} = 220A$
 $R_{DS(on)} \leq 3.5m\Omega$

N-Channel Enhancement Mode
Avalanche Rated



TO-263 (7-lead)



Pins: 1 - Gate
 2, 3 - Source
 5,6,7 - Source
 TAB (8) - Drain

| Symbol | Test Conditions | Maximum Ratings | |
|------------|---|-----------------|------------|
| V_{DSS} | $T_J = 25^\circ C$ to $175^\circ C$ | 40 | V |
| V_{DGR} | $T_J = 25^\circ C$ to $175^\circ C$, $R_{GS} = 1M\Omega$ | 40 | V |
| V_{GSM} | Transient | ± 20 | V |
| I_{D25} | $T_C = 25^\circ C$ | 220 | A |
| I_{LRMS} | Lead Current Limit, RMS | 160 | A |
| I_{DM} | $T_C = 25^\circ C$, pulse width limited by T_{JM} | 660 | A |
| I_{AR} | $T_C = 25^\circ C$ | 110 | A |
| E_{AS} | $T_C = 25^\circ C$ | 600 | mJ |
| P_D | $T_C = 25^\circ C$ | 360 | W |
| T_J | | -55 ... +175 | $^\circ C$ |
| T_{JM} | | 175 | $^\circ C$ |
| T_{stg} | | -55 ... +175 | $^\circ C$ |
| T_L | 1.6mm (0.062in.) from case for 10s | 300 | $^\circ C$ |
| T_{SOLD} | Plastic body for 10 seconds | 260 | $^\circ C$ |
| Weight | | 3 | g |

Features

- International standard package
- $175^\circ C$ Operating Temperature
- High current handling capability
- Avalanche Rated
- Low $R_{DS(on)}$

Advantages

- Easy to mount
- Space savings
- High power density

Applications

- Synchronous Buck Converters
- High Current Switching Power Supplies
- Battery Powered Electric Motors
- Resonant-mode power supplies
- Electronics Ballast Application
- Class D Audio Amplifiers

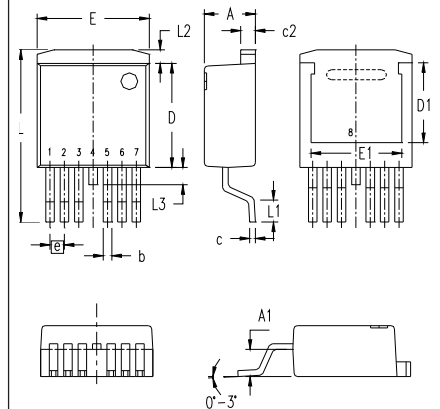
| Symbol | Test Conditions ($T_J = 25^\circ C$ unless otherwise specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|--------------|
| | | Min. | Typ. | Max. |
| BV_{DSS} | $V_{GS} = 0V$, $I_D = 250\mu A$ | 40 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 250\mu A$ | 2.0 | | 4.0 V |
| I_{GSS} | $V_{GS} = \pm 20V$, $V_{DS} = 0V$ | | | ± 200 nA |
| I_{DSS} | $V_{DS} = V_{DSS}$ | | | 5 μA |
| | $V_{GS} = 0V$ $T_J = 150^\circ C$ | | | 50 μA |
| $R_{DS(on)}$ | $V_{GS} = 10V$, $I_D = 50A$, Notes 1, 2 | 2.8 | 3.5 | $m\Omega$ |

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified) | Characteristic Values | | |
|--------------|--|-----------------------|------|--------------------|
| | | Min. | Typ. | Max. |
| g_{fs} | $V_{DS} = 10\text{V}, I_D = 60\text{A}$, Note 1 | 40 | 66 | S |
| C_{iss} | $V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$ | | 6820 | pF |
| C_{oss} | | | 1185 | pF |
| C_{rss} | | | 250 | pF |
| $t_{d(on)}$ | Resistive Switching Times $V_{GS} = 10\text{V}, V_{DS} = 20\text{V}, I_D = 50\text{A}$ $R_G = 3.3\Omega$ (External) | | 15 | ns |
| t_r | | | 21 | ns |
| $t_{d(off)}$ | | | 31 | ns |
| t_f | | | 21 | ns |
| $Q_{g(on)}$ | $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ | | 112 | nC |
| Q_{gs} | | | 33 | nC |
| Q_{gd} | | | 30 | nC |
| R_{thJC} | | | 0.42 | $^\circ\text{C/W}$ |

Source-Drain Diode

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified) | Characteristic Values | | |
|----------|---|-----------------------|------|-------|
| | | Min. | Typ. | Max. |
| I_s | $V_{GS} = 0\text{V}$ | | | 220 A |
| I_{SM} | Repetitive, Pulse width limited by T_{JM} | | | 660 A |
| V_{SD} | $I_F = 50\text{A}, V_{GS} = 0\text{V}$, Note 1 | | | 1.0 V |
| t_{rr} | $I_F = 110\text{A}, V_{GS} = 0\text{V}$ $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 20\text{V}$ | | 45 | ns |
| I_{RM} | | | 1.4 | A |
| Q_{RM} | | | 32 | nC |

TO-263 (7-lead) (IXTA..7) Outline



- Pins: 1 - Gate
2, 3 - Source
4 - Drain
5,6,7 - Source
Tab (8) - Drain

| SYM | INCHES | | MILLIMETER | |
|-----|----------|------|------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .170 | .185 | 4.30 | 4.70 |
| A1 | .085 | .104 | 2.15 | 2.65 |
| b | .026 | .035 | 0.65 | 0.90 |
| c | .016 | .024 | 0.40 | 0.60 |
| c2 | .049 | .055 | 1.25 | 1.40 |
| D | .355 | .370 | 9.00 | 9.40 |
| D1 | .272 | .280 | 6.90 | 7.10 |
| E | .386 | .402 | 9.80 | 10.20 |
| E1 | .311 | .319 | 7.90 | 8.10 |
| e | .050 BSC | | 1.27 BSC | |
| L | .591 | .614 | 15.00 | 15.60 |
| L1 | .091 | .110 | 2.30 | 2.80 |
| L2 | .039 | .059 | 1.00 | 1.50 |
| L3 | .000 | .059 | 0.00 | 1.50 |

- Notes: 1. Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.
2. On through-hole packages, $R_{DS(on)}$ Kelvin test contact location must be 5mm or less from the package body.

IXYS reserves the right to change limits, test conditions, and dimensions.

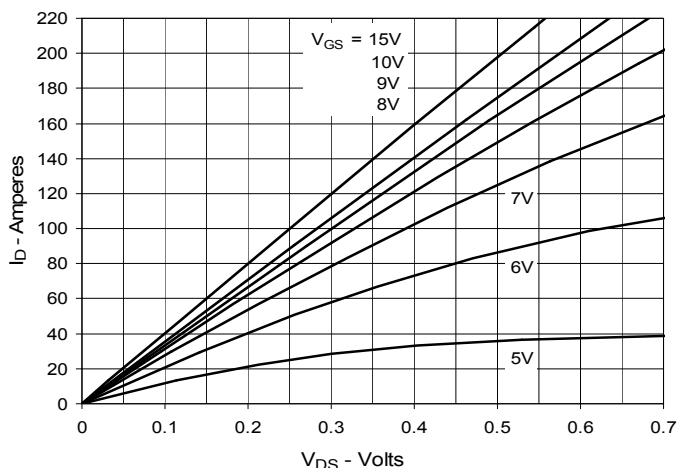
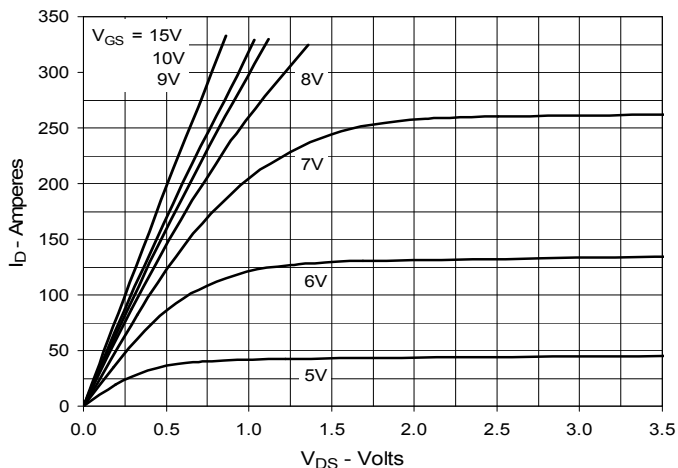
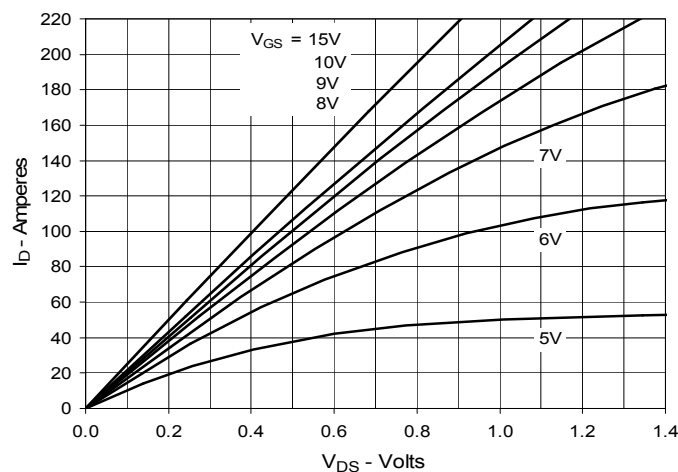
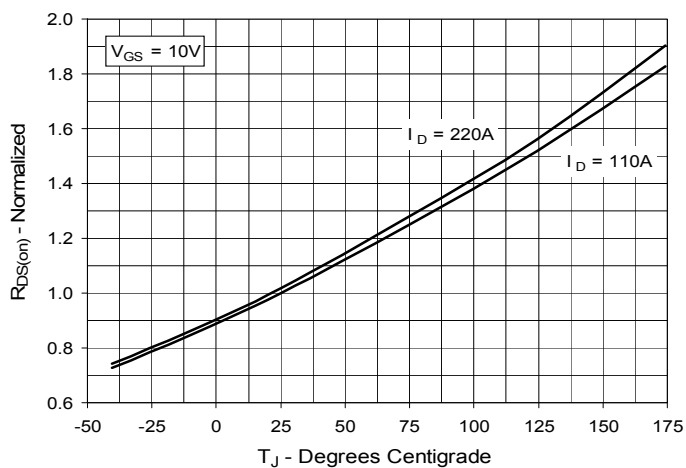
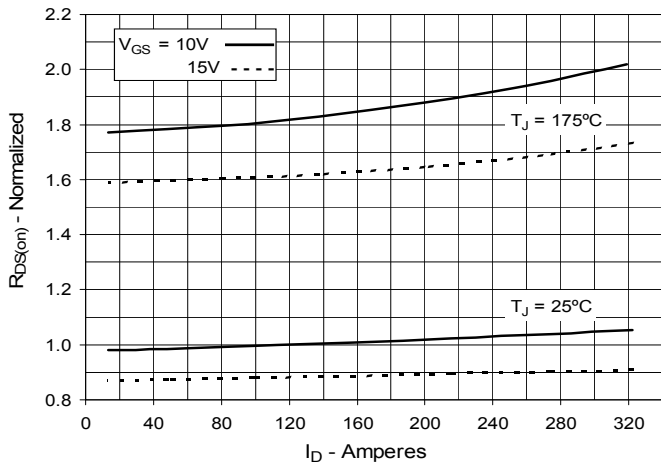
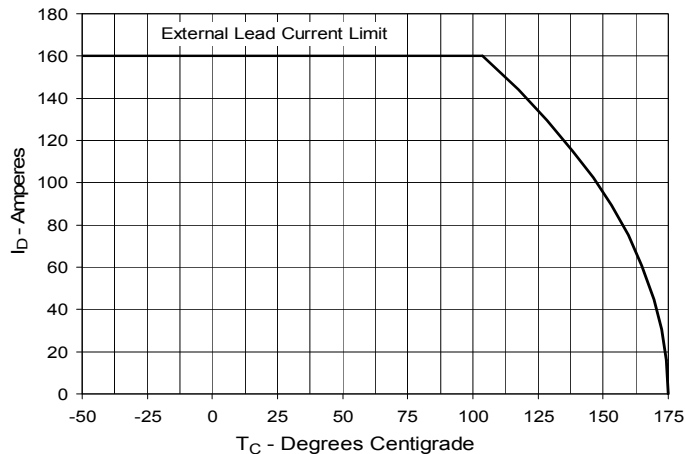
Fig. 1. Output Characteristics @ 25°C

Fig. 2. Extended Output Characteristics @ 25°C

Fig. 3. Output Characteristics @ 150°C

Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 110A$ Value vs. Junction Temperature

Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 110A$ Value vs. Drain Current

Fig. 6. Drain Current vs. Case Temperature


Fig. 7. Input Admittance

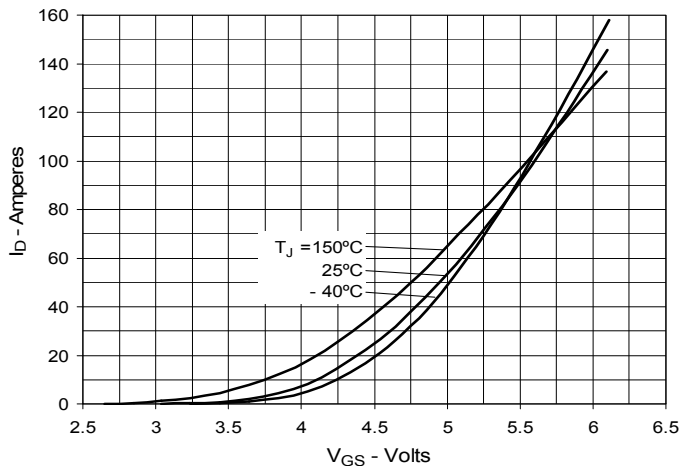


Fig. 8. Transconductance

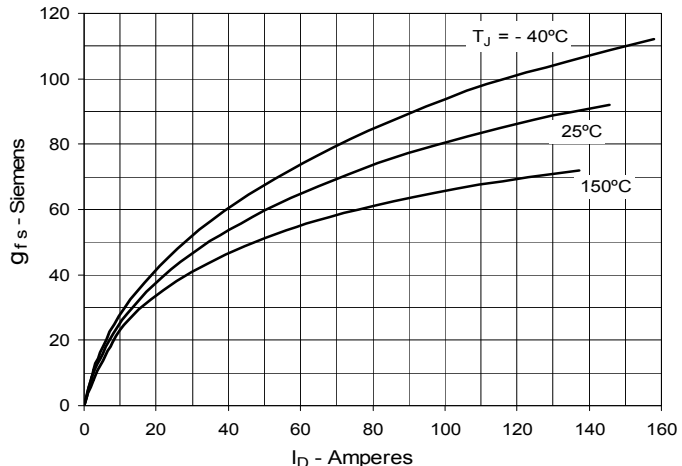


Fig. 9. Forward Voltage Drop of Intrinsic Diode

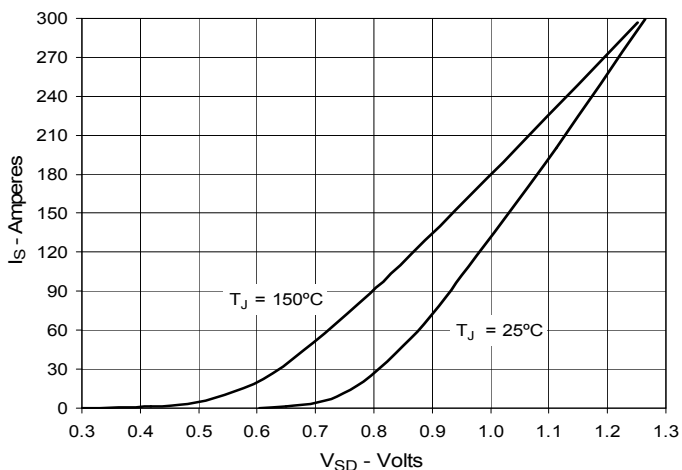


Fig. 10. Gate Charge

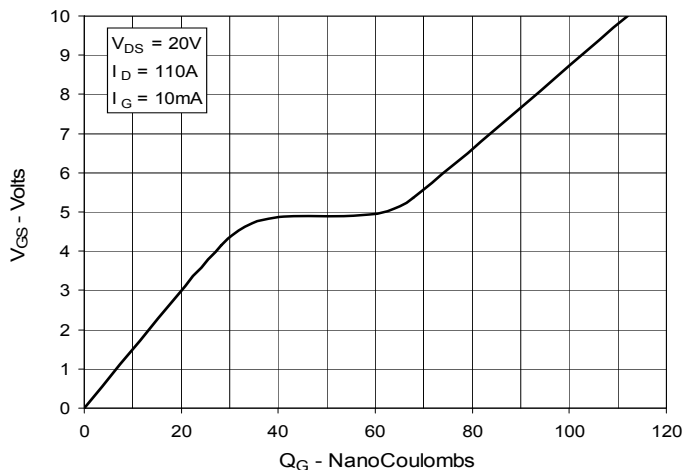


Fig. 11. Capacitance

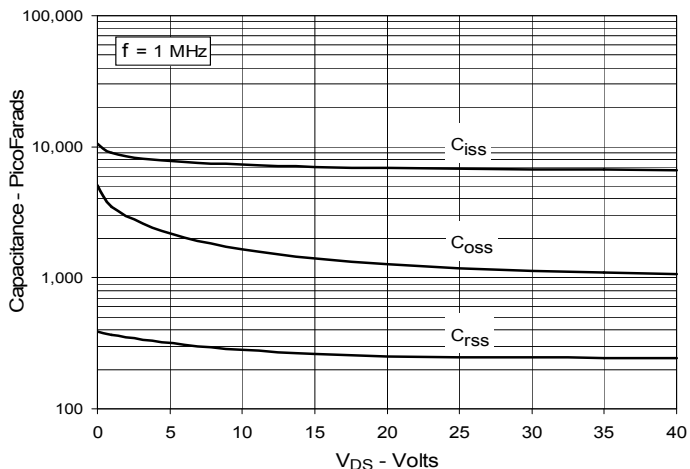


Fig. 12. Forward-Bias Safe Operating Area

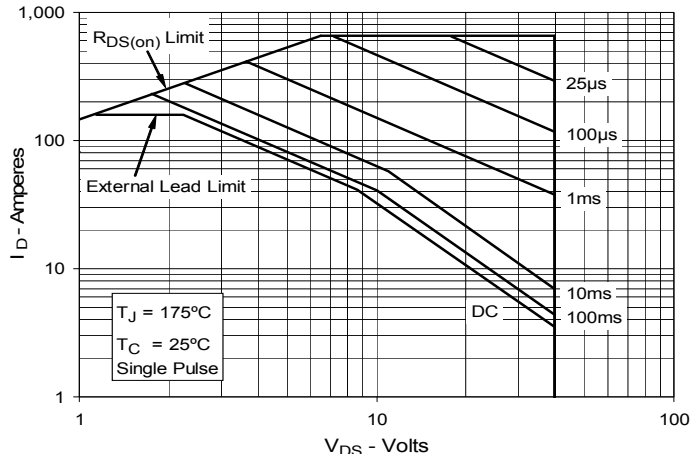


Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

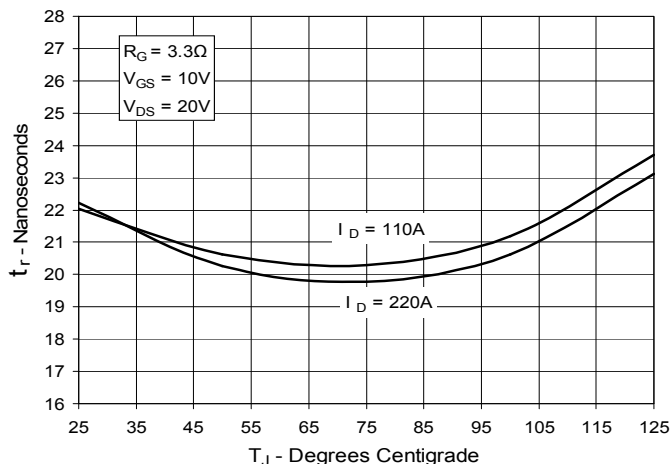


Fig. 14. Resistive Turn-on Rise Time vs. Drain Current

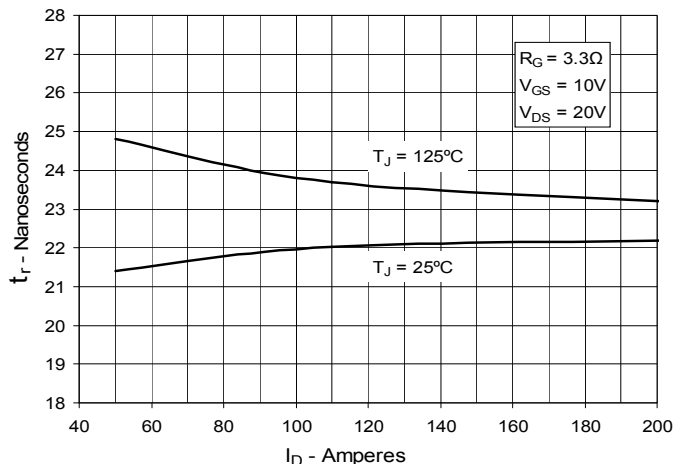


Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

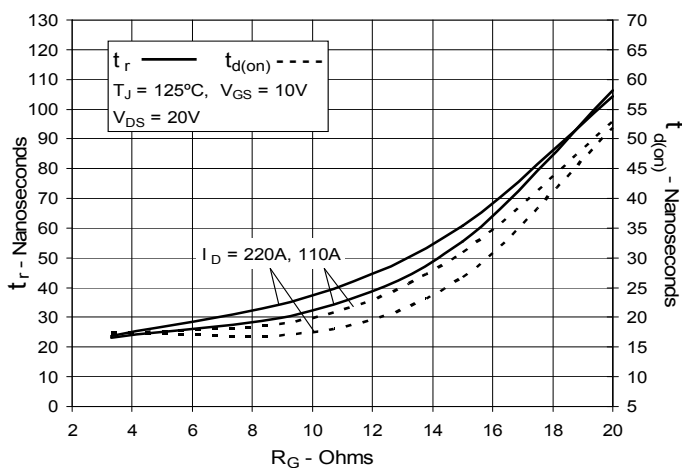


Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

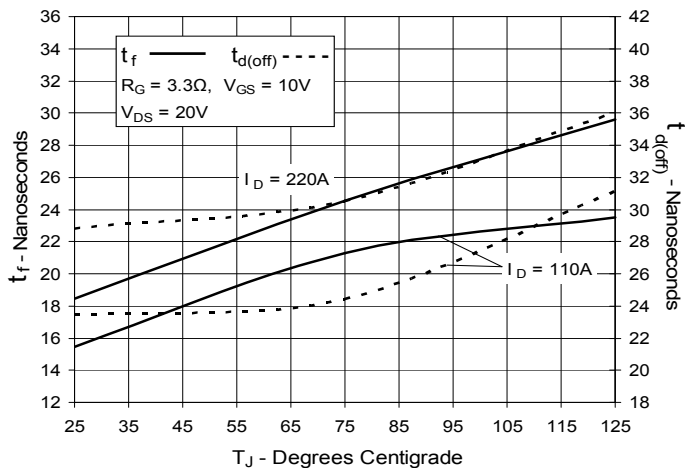


Fig. 17. Resistive Turn-off Switching Times vs. Drain Current

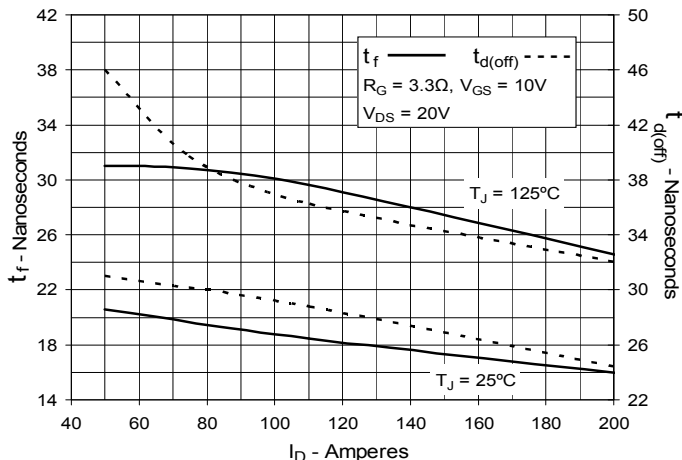


Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance

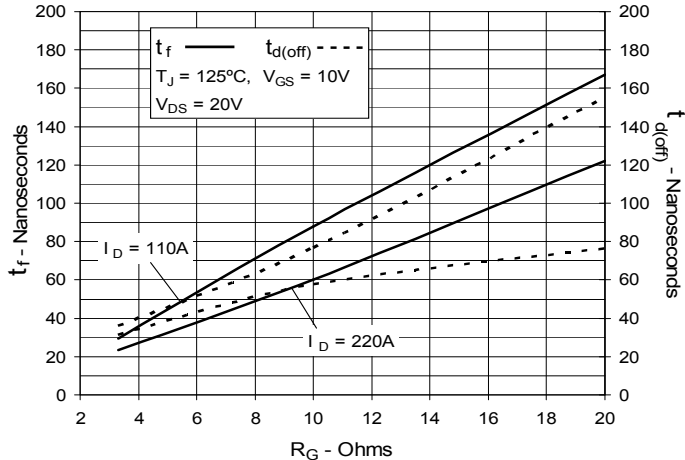


Fig. 19. Maximum Transient Thermal Impedance

